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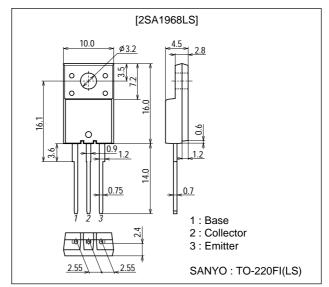
High-Voltage Amplifier, High-Voltage Switching Applications

Features

- · High breakdown voltage(VCEO min=-900V).
- Small Cob(Cob typ=2.2pF).
- High reliability(Adoption of HVP process).
- · Package of full isolation type.

Package Dimensions

unit : mm 2079D



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-900	V
Collector-to-Emitter Voltage	VCEO		-900	V
Emitter-to-Base Voltage	VEBO		-7	V
Collector Current	IC		-10	mA
Collector Current (Pulse)	ICP		-30	mA
Collector Dissipation	PC		2	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =-900V, I _E =0			-1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =-5V, I _C =0			-1	μΑ

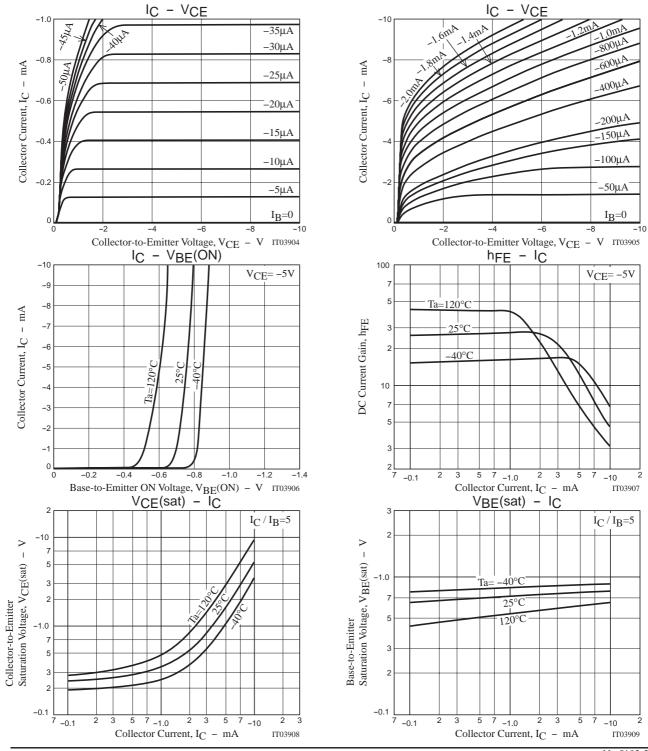
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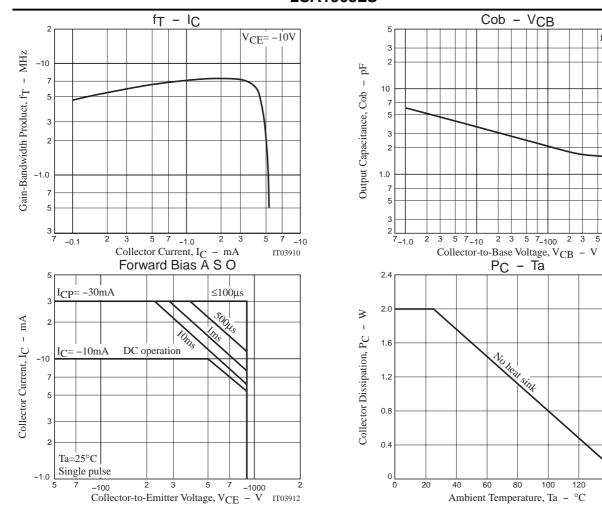
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
DC Current Gain	hFE	V _{CE} =-5V, I _C =-1mA	20		50	
Gain-Bandwidth Product	fŢ	V _{CE} =-10V, I _C =-1mA		6		MHz
Output Capacitance	Cob	V _{CB} =-100V, f=1MHz		2.2		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =-500μA, I _B =-100μA			-1	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =-500μA, I _B =-100μA			-1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=-100μA, IE=0	-900			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-900			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-100μA, I _C =0	-7			V
Transient Thermal Resistance	Rth(j-c)	junction-case			8.3	°C / W



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f=1MHz

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